

## Single-Output LDO Regulators

# **Ultra Low Quiescent Current LDO** Regulator

#### BD7xxL2EFJ-C BD7xxU2EFJ-C BD7xxL2FP-C BD7xxL2FP3-C

#### General Description

The BD7xxL2EFJ-C, BD7xxU2EFJ-C, BD7xxL2FP-C, BD7xxL2FP3-C are low quiescent regulators featuring 50V absolute maximum voltage, and output voltage accuracy of ±2%, 200mA output current and 6µA (Typ) current consumption. These regulators are therefore ideal for applications requiring a direct connection to the battery and a low current consumption. Ceramic capacitors can be used for compensation of the output capacitor phase. Furthermore, these ICs also feature overcurrent protection to protect the device from damage caused by short-circuiting and an integrated thermal shutdown to protect the device from overheating at overload conditions.

### Features

- Ultra low quiescent current: 6µA (Typ)
- Output current capability: 200mA
- Output voltage: 3.3 V or 5.0 V (Typ)
- High output voltage accuracy: ±2%
- Low saturation voltage by using PMOS output
- Integrated overcurrent protection to protect the IC from damage caused by output short-circuiting.
- Integrated thermal shutdown to protect the IC from overheating at overload conditions.
- Low ESR ceramic capacitor can be used as output capacitor.
- HTSOP-J8, TO252-3, SOT223-4(F)(\*1) 3type package

(\*1 : SOT223-4, SOT223-4F)

#### Key specification

Ultra low quiescent current:

6µA (Typ)

Output voltage:

3.3 V or 5.0 V (Typ)

Output current capability:

200mA

High output voltage accuracy: Low ESR ceramic capacitor

can be used as output capacitor

AEC-Q100 Qualified(\*2) (\*2:Grade1)

### Packages

EFJ: HTSOP-J8

W (Typ) x D (Typ) x H (Max) 4.90mm x 6.00mm x 1.00mm



FP: TO252-3

6.50mm x 9.50mm x 2.50mm



FP3: SOT223-4(F)

6.53mm x 7.00mm x 1.80mm



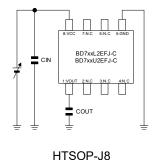
Figure 1. Package Outlook

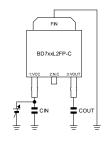
#### Applications

Automotive (body, audio system, navigation system, etc.)

#### Typical Application Circuits

Components externally connected: 0.1 µF ≤ CIN, 4.7 µF ≤ COUT (Min) \*Electrolytic, tantalum and ceramic capacitors can be used.





TO252-3

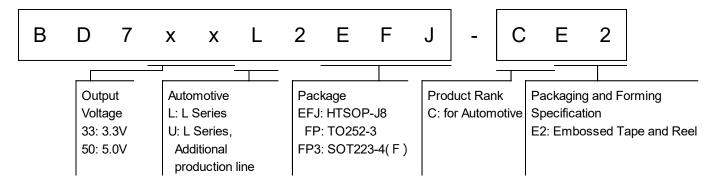
Figure 2. Typical Application Circuits

OProduct structure: Silicon monolithic integrated circuit OThis product is not designed protection against radioactive rays

SOT223-4(F)

BD7xxL2FP3-C

### Ordering Information



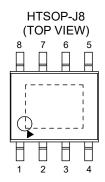
### ●Lineup

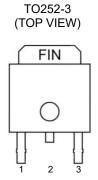
Output current ability	Output voltage (Typ)	Package type	Orderable Part Number	Remarks
		HTSOP-J8	BD733L2EFJ-CE2	Production LineA (Note 1)
	2.2.1	HTSOP-J8	BD733U2EFJ-CE2	Production LineB (Note 1)
	3.3 V	TO252-3	BD733L2FP-CE2	
000 4		SOT223-4(F)	BD733L2FP3-CE2	
200 mA		HTSOP-J8	BD750L2EFJ-CE2	Production LineA (Note 1)
	501/	HTSOP-J8	BD750U2EFJ-CE2	Production LineB (Note 1)
	5.0 V	TO252-3	BD750L2FP-CE2	
		SOT223-4(F)	BD750L2FP3-CE2	

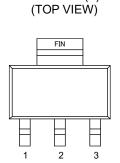
(Note 1) For the purpose of improving production efficiency, Production Line A and B have a multi-line configuration.

Electric characteristics noted in Datasheet does not differ between Production Line A and B. Production Line B is recommended for new product.

### ●Pin Configuration







SOT223-4(F)

Figure 3. Pin Configuration

### **●**Pin Description

### ■HTSOP-J8

Pin No.	Pin Name	Function
1	VOUT	Output pin
2	N.C.	Not connected
3	N.C.	Not connected
4	N.C.	Not connected
5	GND	GND
6	N.C.	Not connected
7	N.C.	Not connected
8	VCC	Supply voltage input pin

(%N.C. terminals are not need to connect to GND. (%Exposed die pad is need to be connected to GND in the inside of IC.) (%Exposed die pad is connected to GND in the inside of IC.)

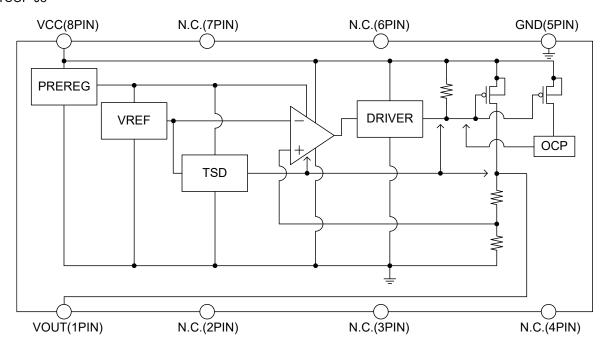
### ■TO252-3, SOT223-4(F)

Pin No.	Pin Name	Function
1	VCC	Supply voltage input pin
2	N.C./GND	TO252-3: N.C. SOT223-4(F): GND
3	VOUT	Output pin
FIN	GND	GND

(%N.C. terminals are not need to connect to GND.)

### ●Block Diagram

### ■HTSOP-J8



### ■TO252-3, SOT223-4(F)

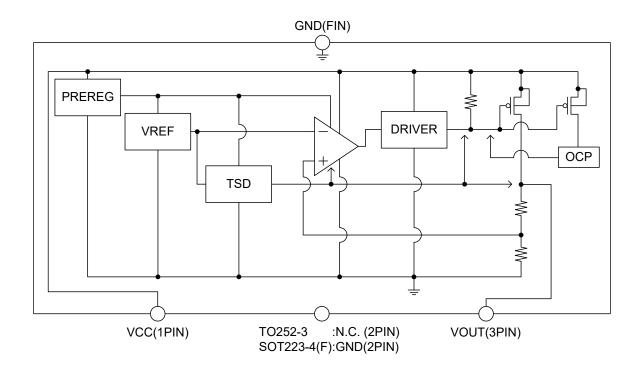


Figure 4. Block Diagram

● Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Supply Voltage *1	VCC	-0.3 to +50.0	V
Operating Temperature Range	Topr	-40 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Maximum Junction Temperature	Tjmax	150	°C

<sup>\*1</sup> Pd should not be exceeded.

### ●Operating Conditions (-40 < Ta < +125°C)

### ■BD733L2EFJ-C, BD733U2EFJ-C, BD733L2FP-C, BD733L2FP3-C

Parameter	Symbol	Min	Max	Unit
Supply Voltage *2	VCC	4.37	45.0	V
Startup Voltage *3	VCC	3.0	-	V
Output Current	IOUT	0	200	mA

#### ■BD750L2EFJ-C, BD750U2EFJ-C, BD750L2FP-C, BD750L2FP3-C

Parameter	Symbol	Min	Max	Unit
Supply Voltage *2	VCC	5.8	45.0	V
Startup Voltage *3	VCC	3.0	-	V
Output Current	IOUT	0	200	mA

<sup>\*2</sup> For output voltage, refer to the dropout voltage corresponding to the output current.

<sup>\*3</sup> When IOUT=0mA.

### ●Thermal Resistance(\*1)

Davanatan	Cymahal	Thermal Re	1.1	
Parameter	Symbol	1s <sup>(*3)</sup>	2s2p <sup>(*4)</sup>	Unit
HTSOP-J8				
Junction to Ambient	θЈА	130	34	°C/W
Junction to Top Characterization Parameter <sup>(*2)</sup>	Ψ <sub>JT</sub>	15	7	°C/W
TO252-3				
Junction to Ambient	θЈА	136	23	°C/W
Junction to Top Characterization Parameter <sup>(*2)</sup>	Ψ <sub>JT</sub>	17	3	°C/W
SOT223-4(F)				
Junction to Ambient	θЈΑ	164	71	°C/W
Junction to Top Characterization Parameter <sup>(*2)</sup>	Ψ <sub>JT</sub>	20	14	°C/W

<sup>(\*1)</sup>Based on JESD51-2A(Still-Air).

**Footprints and Traces** 

Layer Number of Measurement Board	Material	Board Size
Single	FR-4	114.3mm x 76.2mm x 1.57mmt
Тор		
Copper Pattern	Thickness	

70µm

(\*4)Using a PCB board based on JESD51-5. 7

Layer Number of	,	Daniel Cina		Thermal \	/ia <sup>(*5)</sup>
Measurement Board	Material	Board Size		Pitch	Diameter
4 Layers	FR-4	114.3mm x 76.2mm	114.3mm x 76.2mm x 1.6mmt 1.20mm		Ф0.30mm
Тор					
Тор		2 Internal Laye	ers	Bottor	n
Top Copper Pattern	Thickness	2 Internal Laye Copper Pattern	ers Thickness	Bottor Copper Pattern	Thickness

<sup>(\*5)</sup> This thermal via connects with the copper pattern of all layers.

<sup>(\*2)</sup>The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package.
(\*3)Using a PCB board based on JESD51-3.

### ● Electrical Characteristics (BD733L2EFJ-C, BD733U2EFJ-C, BD733L2FP-C, BD733L2FP3-C)

(Unless otherwise specified, -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA, Reference value: Ta=25°C)

Deremeter	Cymphol	Limit			Unit	Conditions
Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Bias current	lb	-	6	15	μΑ	
Output voltage	VOUT	3.23	3.30	3.37	V	8V < VCC < 16V 0mA < IOUT < 100mA
Dropout voltage	ΔVd	-	0.6	1.0	V	VCC=VOUT×0.95, IOUT=200mA
Ripple rejection	R.R.	50	63	-	dB	f=120Hz, ein=1Vrms, IOUT=100mA
Line regulation	Reg I	-	5	20	mV	8V < VCC < 16V
Load regulation	Reg L	-	5	20	mV	10mA < IOUT < 200mA

### ● Electrical Characteristics (BD750L2EFJ-C, BD750U2EFJ-C, BD750L2FP-C, BD750L2FP3-C)

(Unless otherwise specified, -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA, Reference value: Ta=25°C)

Dansaratan	O b I	Limit			1.1	0 111
Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Bias current	lb	-	6	15	μΑ	
Output voltage	VOUT	4.9	5.0	5.1	V	8V < VCC < 16V 0mA < IOUT < 100mA
Dropout voltage	ΔVd	-	0.4	0.7	V	VCC=VOUT×0.95, IOUT=200mA
Ripple rejection	R.R.	50	60	-	dB	f=120Hz, ein=1Vrms, IOUT=100mA
Line regulation	Reg I	-	5	20	mV	8V < VCC < 16V
Load regulation	Reg L	-	5	20	mV	10mA < IOUT < 200mA

### **●**Typical Performance Curves

■BD733L2EFJ-C, BD733U2EFJ-C, BD733L2FP-C, BD733L2FP3-C Reference data Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA

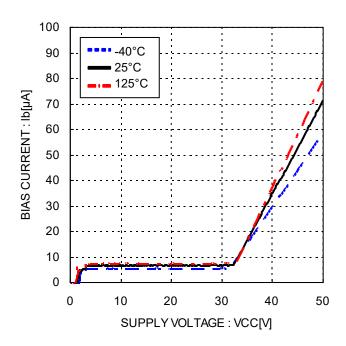


Figure 5. Bias current

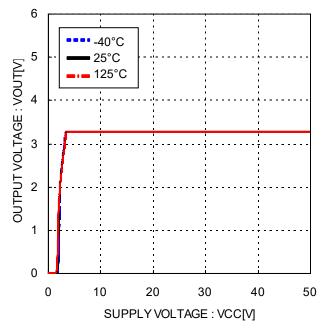


Figure 7. Output voltage vs. Supply voltage IOUT=100mA

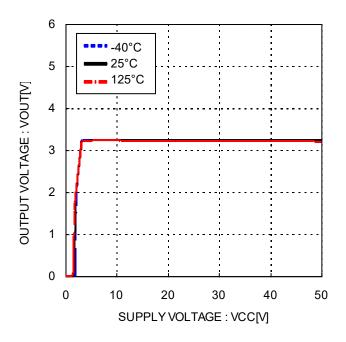


Figure 6. Output voltage vs. Supply voltage IOUT=10mA

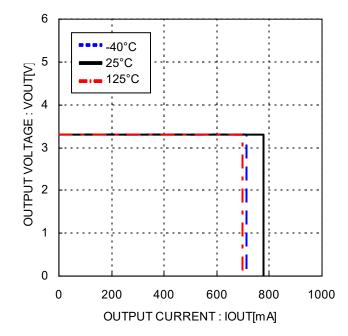
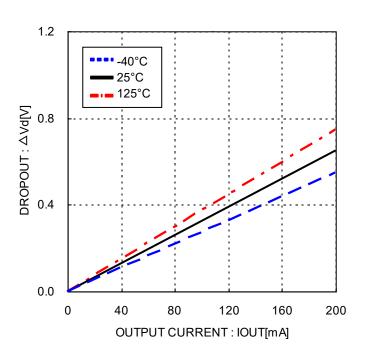


Figure 8. Output voltage vs. Load

■BD733L2EFJ-C, BD733U2EFJ-C, BD733L2FP-C, BD733L2FP3-C Reference data Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA



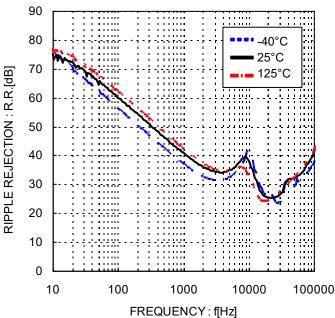


Figure 9. Dropout voltage

Figure 10. Ripple rejection (ein=1Vrms,IOUT=100mA)

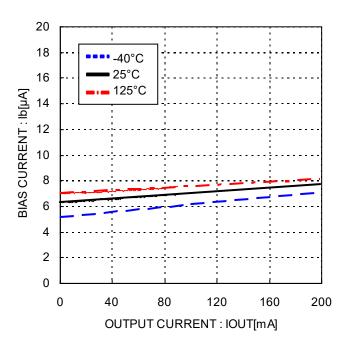


Figure 11. Total supply current vs. Load

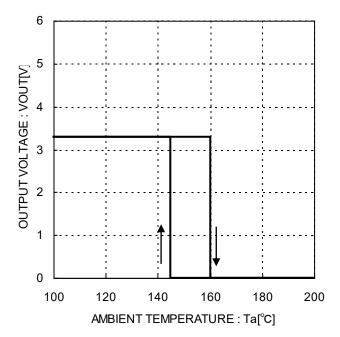
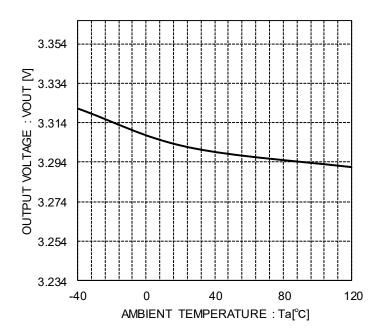


Figure 12. Thermal shutdown (Output voltage vs. Temperature)

■BD733L2EFJ-C, BD733U2EFJ-C, BD733L2FP-C, BD733L2FP3-C Reference data Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA



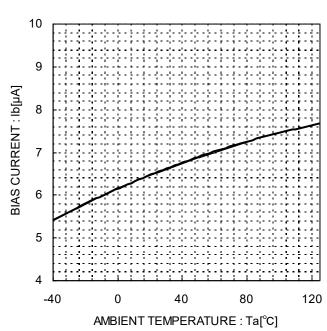


Figure 13. Output voltage vs. Temperature

Figure 14. Bias current vs. Temperature

■BD750L2EFJ-C, BD750U2EFJ-C, BD750L2FP-C, BD750L2FP3-C Reference data Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA

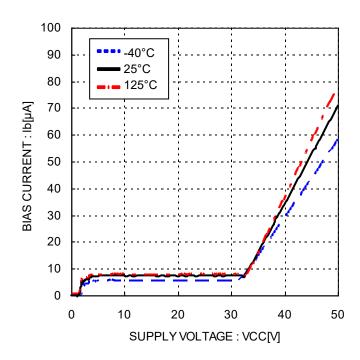


Figure 15. Bias current

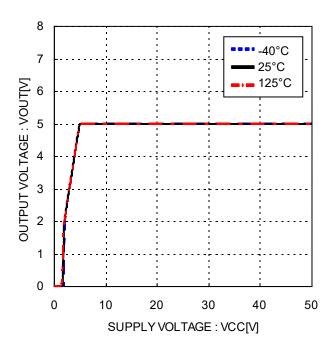


Figure 16. Output voltage vs. Supply voltage

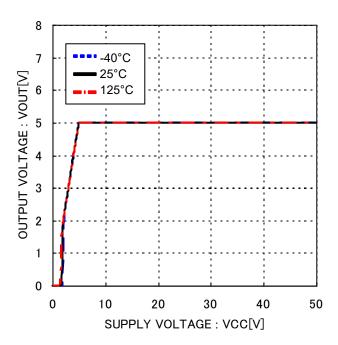


Figure 17. Output voltage vs. Supply voltage IOUT=100mA

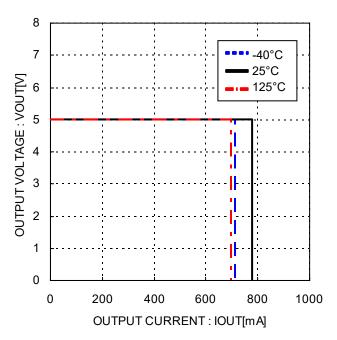
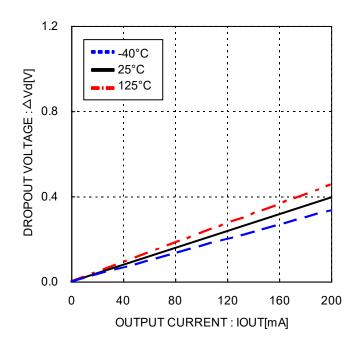


Figure 18. Output voltage vs. Load

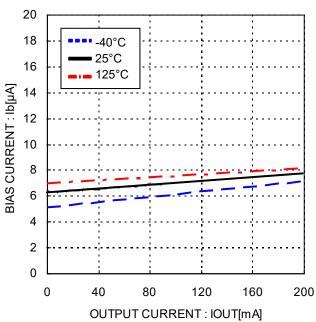
■BD750L2EFJ-C, BD750U2EFJ-C, BD750L2FP-C, BD750L2FP3-C Reference data Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA

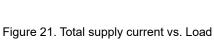


90 40°C 80 25°C RIPPLE REJECTION : R.R.[dB] 70 125°C 60 50 40 30 20 10 0 10 100 1000 10000 100000 FREQUENCY: f[Hz]

Figure 19. Dropout voltage

Figure 20. Ripple rejection (ein=1Vrms,IOUT=100mA)





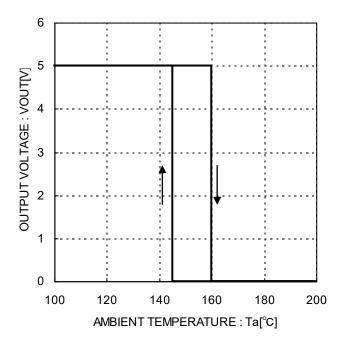
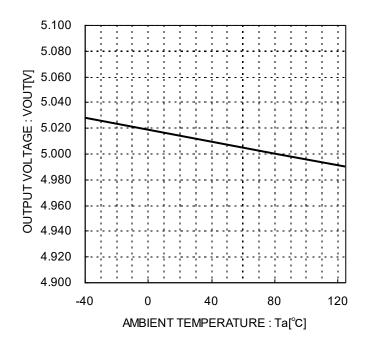


Figure 22. Thermal shutdown (Output voltage vs. Temperature)

■BD750L2EFJ-C, BD750U2EFJ-C, BD750L2FP-C, BD750L2FP3-C Reference data Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA



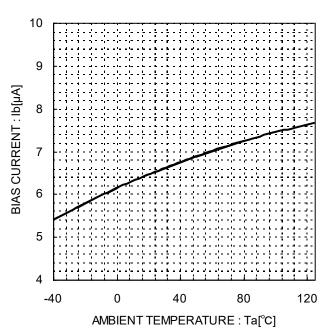
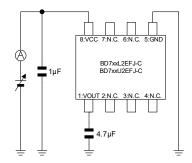


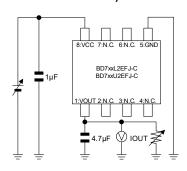
Figure 23. Output voltage vs. Temperature

Figure 24. Bias current vs. Temperature

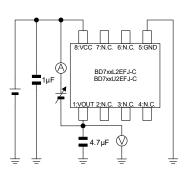
### ● Measurement Circuit (BD7xxL2EFJ-C BD7xxU2EFJ-C Series) HTSOP-J8



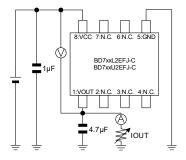
Measurement setup for Figure 5, 14, 15, 24



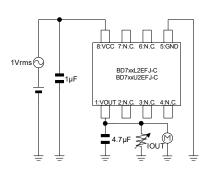
Measurement setup for Figure 6, 7, 12, 13, 16, 17, 22, 23



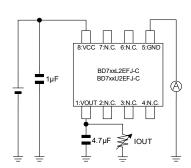
Measurement setup for Figure 8, 18



Measurement setup for Figure 9, 19

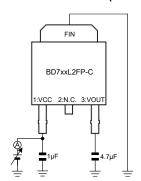


Measurement setup for Figure 10, 20

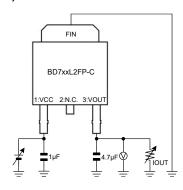


Measurement setup for Figure 11, 21

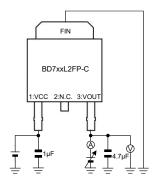
### ● Measurement Circuit (BD7xxL2FP-C Series) TO252-3



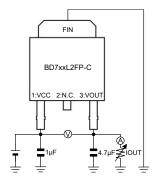
Measurement setup for Figure 5, 14, 15, 24



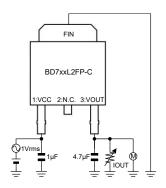
Measurement setup for Figure 6, 7, 12, 13, 16, 17, 22, 23



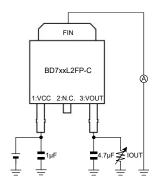
Measurement setup for Figure 8, 18



Measurement setup for Figure 9, 19

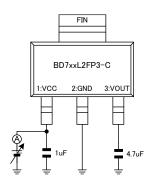


Measurement setup for Figure 10, 20

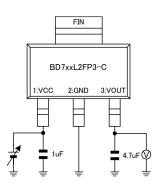


Measurement setup for Figure 11, 21

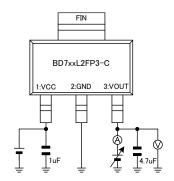
#### ● Measurement Circuit (BD7xxL2FP3-C Series) SOT223-4(F)



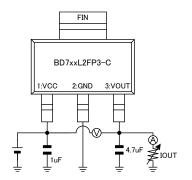
Measurement setup for Figure 5, 14, 15, 24



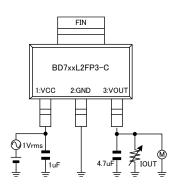
Measurement setup for Figure 6, 7, 12, 13, 16, 17, 22, 23



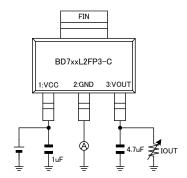
Measurement setup for Figure 8, 18



Measurement setup for Figure 9, 19



Measurement setup for Figure 10, 20



Measurement setup for Figure 11, 21

### Selection of Components Externally Connected

VCC pin

Insert capacitors with a capacitance of  $0.1\mu F$  or higher between the VCC and GND pin. Choose the capacitance according to the line between the power smoothing circuit and the VCC pin. Selection of the capacitance also depends on the application. Verify the application and allow for sufficient margins in the design. We recommend using a capacitor with excellent voltage and temperature characteristics.

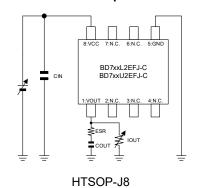
#### · Output pin capacitor

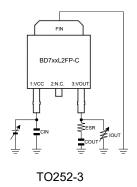
In order to prevent oscillation, a capacitor needs to be placed between the output pin and GND pin. We recommend using a capacitor with a capacitance of  $4.7\mu F$  or higher. Electrolytic, tantalum and ceramic capacitors can be used. When selecting the capacitor ensure that the capacitance of  $4.7\mu F$  or higher is maintained at the intended applied voltage and temperature range. Due to changes in temperature the capacitor's capacitance can fluctuate possibly resulting in oscillation. For selection of the capacitor refer to the IOUT vs. ESR data. The stable operation range given in the reference data is based on the standalone IC and resistive load. For actual applications the stable operating range is influenced by the PCB impedance, input supply impedance and load impedance. Therefore verification of the final operating environment is needed.

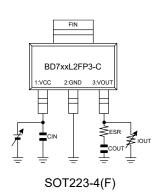
When selecting a ceramic type capacitor, we recommend using X5R, X7R or better with excellent temperature and DC-biasing characteristics and high voltage tolerance.

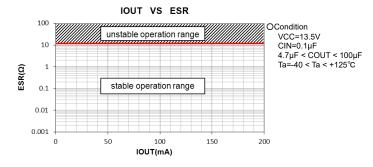
Also, in case of rapidly changing input voltage and load current, select the capacitance in accordance with verifying that the actual application meets with the required specification.

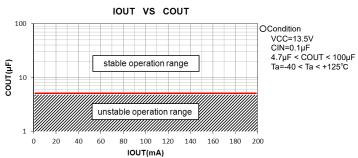
#### Measurement setup











#### Power Dissipation

#### **■**HTSOP-J8

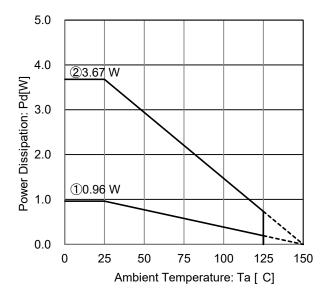


Figure 25. HTSOP-J8 Package Data

IC mounted on ROHM standard board based on JEDEC.

(1) : 1 - layer PCB

(Copper foil area on the reverse side of PCB: 0 mm x 0 mm)

Board material: FR4

Board size: 114.3 mm x 76.2 mm x 1.57 mmt

Mount condition: PCB and exposed pad are soldered.

Top copper foil: ROHM recommended footprint + wiring to measure, 2 oz. copper.

2 : 4 - layer PCB

(2 inner layers and Copper foil area on the reverse side of PCB:

74.2 mm x 74.2 mm) Board material: FR4

Board size: 114.3 mm x 76.2 mm x 1.60 mmt

Mount condition: PCB and exposed pad are soldered.

Top copper foil: ROHM recommended footprint + wiring to measure, 2 oz. copper. 2 inner layers copper foil area of PCB : 74.2 mm x 74.2 mm, 1 oz. copper. Copper foil area on the reverse side of PCB

: 74.2 mm x 74.2 mm, 2 oz. copper.

Condition(1):  $\theta_{JA} = 130 \text{ C} / \text{W}$ ,  $\Psi_{JT}$  (top center) = 15 °C / W Condition(2):  $\theta_{JA} = 34$  C / W,  $\Psi_{JT}$  (top center) = 7 °C / W

#### ■TO252-3

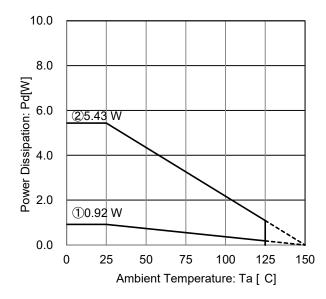


Figure 26. TO252-3 Package Data

IC mounted on ROHM standard board based on JEDEC.

: 1 - layer PCB

(Copper foil area on the reverse side of PCB: 0 mm x 0 mm)

Board material: FR4

Board size: 114.3 mm x 76.2 mm x 1.57 mmt

Mount condition: PCB and exposed pad are soldered.

Top copper foil: ROHM recommended footprint + wiring to measure, 2 oz. copper.

② : 4 - layer PCB

(2 inner layers and Copper foil area on the reverse side of PCB:

74.2 mm x 74.2 mm) Board material: FR4

Board size: 114.3 mm x 76.2 mm x 1.60 mmt

Mount condition: PCB and exposed pad are soldered.

Top copper foil: ROHM recommended footprint + wiring to measure, 2 oz. copper. 2 inner layers copper foil area of PCB : 74.2 mm x 74.2 mm, 1 oz. copper. Copper foil area on the reverse side of PCB

: 74.2 mm x 74.2 mm, 2 oz. copper.

Condition(1):  $\theta_{JA} = 136$  C / W,  $\Psi_{JT}$  (top center) = 17 °C / W Condition(2):  $\theta_{JA} = 23 \, ^{\circ}\text{C} / \text{W}$ .  $\Psi_{JT}$  (top center) =  $3 \, ^{\circ}\text{C} / \text{W}$ 

■SOT223-4(F)

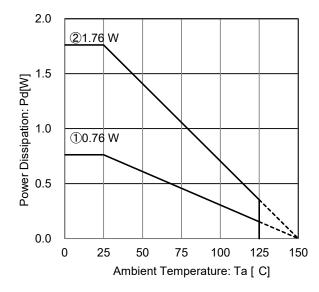


Figure 27. SOT223-4(F) Package Data

IC mounted on ROHM standard board based on JEDEC.

① : 1 - layer PCB

(Copper foil area on the reverse side of PCB: 0 mm x 0 mm)

Board material: FR4

Board size: 114.3 mm x 76.2 mm x 1.57 mm

Mount condition: PCB and exposed pad are soldered.

Top copper foil: ROHM recommended footprint + wiring to measure, 2 oz. copper.

②:4-layer PCB

(2 inner layers and Copper foil area on the reverse side of PCB:

74.2 mm x 74.2 mm) Board material: FR4

Board size: 114.3 mm x 76.2 mm x 1.60 mm

Mount condition: PCB and exposed pad are soldered.

Top copper foil: ROHM recommended footprint + wiring to measure, 2 oz. copper. 2 inner layers copper foil area of PCB: 74.2 mm x 74.2 mm, 1 oz. copper.

Copper foil area on the reverse side of PCB

: 74.2 mm x 74.2 mm, 2 oz. copper.

Condition(1):  $\theta_{JA}$  = 164 C / W,  $\Psi_{JT}$  (top center) = 20 °C / W Condition(2):  $\theta_{JA}$  = 71 C / W,  $\Psi_{JT}$  (top center) = 14 °C / W

Refer to the heat mitigation characteristics illustrated in Figure 25 to Figure 27 when using the IC in an environment of Ta≥25°C. The characteristics of the IC are greatly influenced by the operating temperature, and it is necessary to operate under the maximum junction temperature Timax.

Even if the ambient temperature Ta is at 25°C it is possible that the junction temperature Tj reaches high temperatures. Therefore, the IC should be operated within the power dissipation range.

The following method is used to calculate the power consumption Pc (W)

Pc=(VCC−VOUT)×IOUT+VCC×Ib Power dissipation Pd ≥ Pc

The load current Lo is obtained by operating the IC within the power dissipation range.

VOUT: Output voltage
IOUT: Load current
Ib: Bias current
Ishort: Shorted current

VCC : Input voltage

$$IOUT \le \frac{Pd - VCC \times Ib}{VCC - VOUT}$$

(Refer to Figure 11 and Figure 21 for the lb)

Thus, the maximum load current IOUTmax for the applied voltage VCC can be calculated during the thermal design process.

- ●HTSOP-J8
- ■Calculation example 1) with Ta=125°C, VCC=13.5V, VOUT=3.3V

$$IOUT \le \frac{0.73 - 13.5 \times Ib}{10.2}$$

$$IOUT \le 71.5 \text{mA} \quad \text{(Ib: 6µA)}$$

$$\theta \text{ja=34°C/W} \rightarrow -29.4 \text{mW/°C}$$

$$25°C = 3.67 \text{W} \rightarrow 125°C = 0.73 \text{W}$$

At Ta=125°C with Figure 25 ② condition, the calculation shows that ca 71.5mA of output current is possible at 10.2V potential difference across input and output.

■ Calculation example 2) with Ta=125°C, VCC=13.5V, VOUT=5.0V

IOUT 
$$\leq \frac{0.73 - 13.5 \times \text{lb}}{8.5}$$
  $\theta \text{ja} = 34^{\circ}\text{C/W} \rightarrow -29.4 \text{mW/°C} \\ 25^{\circ}\text{C} = 3.67 \text{W} \rightarrow 125^{\circ}\text{C} = 0.73 \text{W}$ 

At Ta=125°C with Figure 25 ② condition, the calculation shows that ca 85.8mA of output current is possible at 8.5V potential difference across input and output.

The thermal calculation shown above should be taken into consideration during the thermal design in order to keep the whole operating temperature range within the power dissipation range.

In the event of shorting (i.e. VOUT and GND pins are shorted) the power consumption Pc of the IC can be calculated as follows:

Pc=VCC×(lb+lshort) (Refer to Figure 8 and Figure 18 for the Ishort)

- ●TO252-3
- ■Calculation example 3) with Ta=125°C, VCC=13.5V, VOUT=3.3V

At Ta=125°C with Figure 26 ② condition, the calculation shows that ca 105mA of output current is possible at 10.2V potential difference across input and output.

■Calculation example 4) with Ta=125°C, VCC=13.5V, VOUT=5.0V

At Ta=125°C with Figure 26 ② condition, the calculation shows that ca 127mA of output current is possible at 8.5V potential difference across input and output.

The thermal calculation shown above should be taken into consideration during the thermal design in order to keep the whole operating temperature range within the power dissipation range.

In the event of shorting (i.e. VOUT and GND pins are shorted) the power consumption Pc of the IC can be calculated as follows:

Pc=VCC×(lb+lshort) (Refer to Figure 8 and Figure 18 for the lshort)

- ●SOT223-4(F)
- ■Calculation example 5) with Ta=125°C, VCC=13.5V, VOUT=3.3V

IOUT ≤ 
$$\frac{0.35-13.5 \times lb}{10.2}$$
  $\theta$ ja=71°C/W → -14.1mW/°C  $25$ °C=1.76W → 125°C=0.35W

At Ta=125°C with Figure 27 ② condition, the calculation shows that ca 34.3mA of output current is possible at 10.2V potential difference across input and output.

■Calculation example 6) with Ta=125°C, VCC=13.5V, VOUT=5.0V

IOUT ≤ 
$$\frac{0.35-13.5 \times lb}{8.5}$$
  $\theta$ ja=71°C/W → -14.1mW/°C 25°C=1.76W → 125°C=0.35W

At Ta=125°C with Figure 27 ② condition, the calculation shows that ca 41.1mA of output current is possible at 8.5V potential difference across input and output.

The thermal calculation shown above should be taken into consideration during the thermal design in order to keep the whole operating temperature range within the power dissipation range.

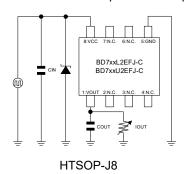
In the event of shorting (i.e. VOUT and GND pins are shorted) the power consumption Pc of the IC can be calculated as follows:

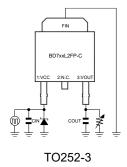
Pc=VCC×(lb+lshort) (Refer to Figure 8 and Figure 18 for the lshort)

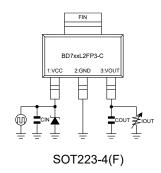
### Application Examples

Applying positive surge to the VCC pin

If the possibility exists that surges higher than 50V will be applied to the VCC pin, a zenar diode should be placed between the VCC pin and GND pin as shown in the figure below.

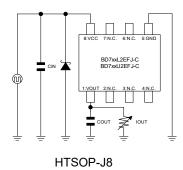


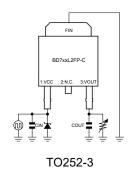


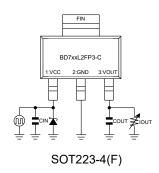


· Applying negative surge to the VCC pin

If the possibility exists that negative surges lower than the GND are applied to the VCC pin, a Shottky diode should be place between the VCC pin and GND pin as shown in the figure below.

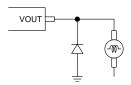






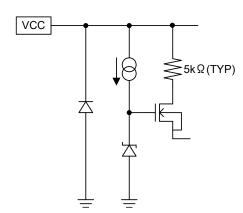
· Implementing a protection diode

If the possibility exists that a large inductive load is connected to the output pin resulting in back-EMF at time of startup and shutdown, a protection diode should be placed as shown in the figure below.

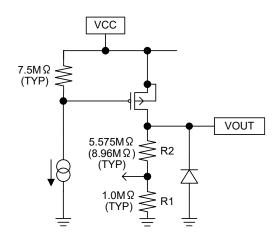


### ●I/O equivalence circuits

### OInput terminal



### OOutput terminal \*inside of () shows 5V



#### Operational Notes

#### 1) Absolute maximum ratings

Exceeding the absolute maximum rating for supply voltage, operating temperature or other parameters can result in damages to or destruction of the chip. In this event it also becomes impossible to determine the cause of the damage (e.g. short circuit, open circuit, etc.). Therefore, if any special mode is being considered with values expected to exceed the absolute maximum ratings, implementing physical safety measures, such as adding fuses, should be considered.

2) The electrical characteristics given in this specification may be influenced by conditions such as temperature, supply voltage and external components. Transient characteristics should be sufficiently verified.

#### 3) GND electric potential

Keep the GND pin potential at the lowest (minimum) level under any operating condition. Furthermore, ensure that, including the transient, none of the pin's voltages are less than the GND pin voltage.

#### 4) GND wiring pattern

When both a small-signal GND and a high current GND are present, single-point grounding (at the set standard point) is recommended. This in order to separate the small-signal and high current patterns and to ensure that voltage changes stemming from the wiring resistance and high current do not cause any voltage change in the small-signal GND. Similarly, care must be taken to avoid wiring pattern fluctuations in any connected external component GND.

#### 5) Inter-pin shorting and mounting errors

Ensure that when mounting the IC on the PCB the direction and position are correct. Incorrect mounting may result in damaging the IC. Also, shorts caused by dust entering between the output, input and GND pin may result in damaging the IC.

#### 6) Inspection using the set board

The IC needs to be discharged after each inspection process as, while using the set board for inspection, connecting a capacitor to a low-impedance pin may cause stress to the IC. As a protection from static electricity, ensure that the assembly setup is grounded and take sufficient caution with transportation and storage. Also, make sure to turn off the power supply when connecting and disconnecting the inspection equipment.

### 7) Thermal design

The power dissipation under actual operating conditions should be taken into consideration and a sufficient margin should be allowed for in the thermal design. On the reverse side of the package this product has an exposed heat pad for improving the heat dissipation. Use both the front and reverse side of the PCB to increase the heat dissipation pattern as far as possible. The amount of heat generated depends on the voltage difference across the input and output, load current, and bias current. Therefore, when actually using the chip, ensure that the generated heat does not exceed the Pd rating. Should by any condition the maximum junction temperature rating be exceeded by the temperature increase of the chip, it may result in deterioration of the properties of the chip. The thermal impedance in this specification is based on recommended PCB and measurement condition by JEDEC standard. Verify the application and allow sufficient margins in the thermal design.

Tjmax: maximum junction temperature=150°C, Ta: ambient temperature (°C), θja: junction-to-ambient thermal resistance (°C/W), Pd: power dissipation rating (W), Pc: power consumption (W), VCC: input voltage, VOUT: output voltage, IOUT: load current, Ib: bias current

Power dissipation rating Pd (W)= $(Tjmax-Ta)/\theta ja$ Power consumption Pc (W)= $(VCC-VOUT)\times IOUT+VCC\times Ib$ 

#### 8) Rapid variation in VCC voltage and load current

In case of a rapidly changing input voltage, transients in the output voltage might occur due to the use of a MOSFET as output transistor. Although the actual application might be the cause of the transients, the IC input voltage, output current and temperature are also possible causes. In case problems arise within the actual operating range, use countermeasures such as adjusting the output capacitance.

#### 9) Minute variation in output voltage

In case of using an application susceptible to minute changes to the output voltage due to noise, changes in input and load current, etc., use countermeasures such as implementing filters.

#### 10) Overcurrent protection circuit

This IC incorporates an integrated overcurrent protection circuit that is activated when the load is shorted. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection circuit.

#### 11) Thermal shutdown (TSD)

This IC incorporates and integrated thermal shutdown circuit to prevent heat damage to the IC. Normal operation should be within the power dissipation rating, if however the rating is exceeded for a continued period, the junction temperature (Tj) will rise and the TSD circuit will be activated and turn all output pins OFF. After the Tj falls below the TSD threshold the circuits are automatically restored to normal operation.

Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

- 12) In some applications, the VCC and pin potential might be reversed, possibly resulting in circuit internal damage or damage to the elements. For example, while the external capacitor is charged, the VCC shorts to the GND. Use a capacitor with a capacitance with less than 1000μF. We also recommend using reverse polarity diodes in series or a bypass between all pins and the VCC pin.
- 13) This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P/N junctions are formed at the intersection of these P layers with the N layers of other elements to create a variety of parasitic elements.

For example, in case a resistor and a transistor are connected to the pins as shown in the figure below then:

- o The P/N junction functions as a parasitic diode when GND > pin A for the resistor, or GND > pin B for the transistor.
- o Also, when GND > pin B for the transistor (NPN), the parasitic diode described above combines with the N layer of the other adjacent elements to operate as a parasitic NPN transistor.

Parasitic diodes inevitably occur in the structure of the IC. Their operation can result in mutual interference between circuits and can cause malfunctions and, in turn, physical damage to or destruction of the chip. Therefore do not employ any method in which parasitic diodes can operate such as applying a voltage to an input pin that is lower than the (P substrate) GND.

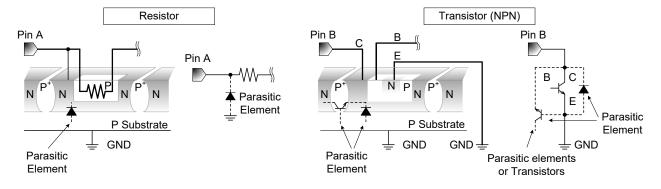
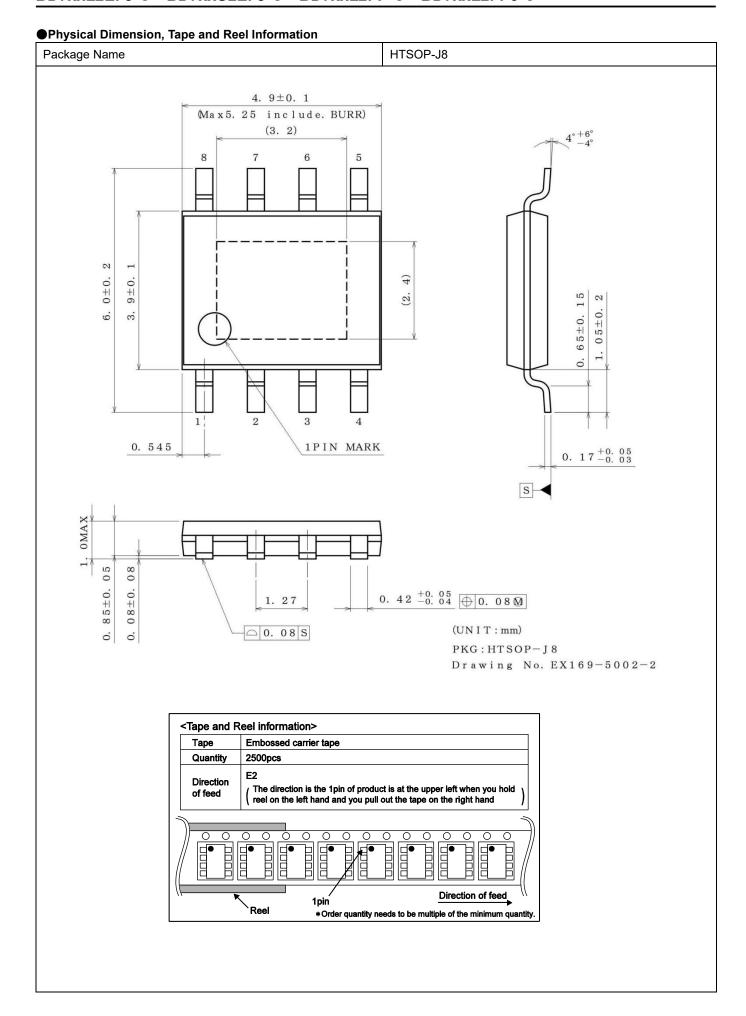
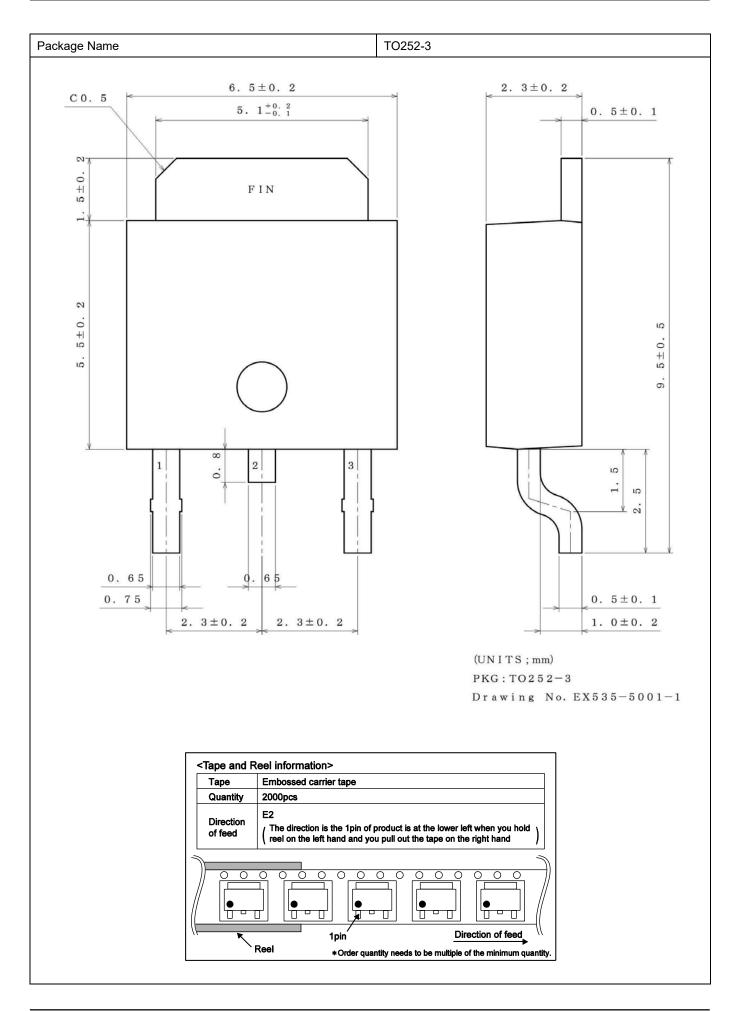
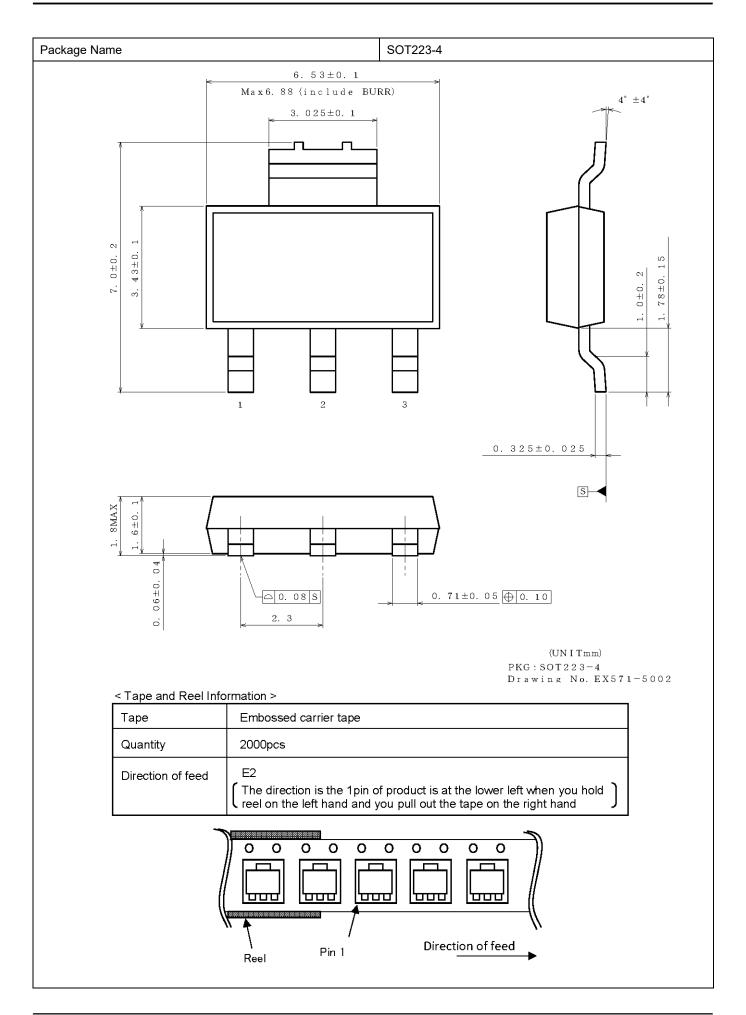
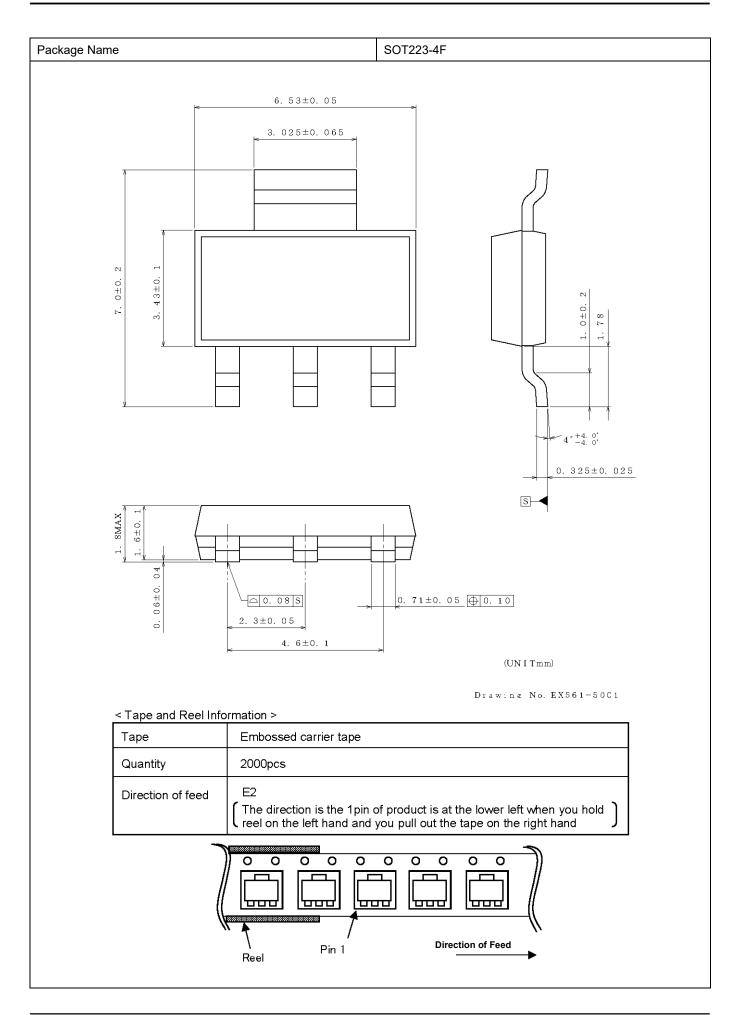


Figure 28. Example of the Parasitic Device Structures



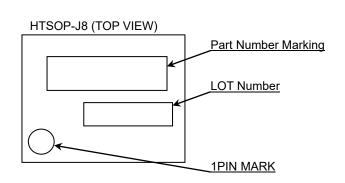


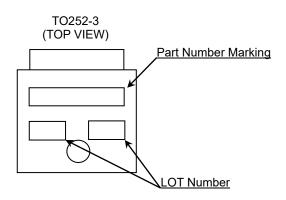




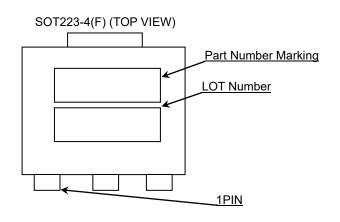
### Marking Diagrams

#### HTSOP-J8 T0252-3





### SOT223-4(F)



Orderable Part Number	Part Number Marking	Output Voltage (V)	Package
BD733L2EFJ-CE2	D733L2		HTSOP-J8
BD733U2EFJ-CE2	D733U2	2.2	HTSOP-J8
BD733L2FP-CE2	BD733L2	3.3	TO252-3
BD733L2FP3-CE2	BD733L2		SOT223-4(F)
BD750L2EFJ-CE2	D750L2		HTSOP-J8
BD750U2EFJ-CE2	D750U2	5.0	HTSOP-J8
BD750L2FP-CE2	BD750L2	5.0	TO252-3
BD750L2FP3-CE2	BD750L2		SOT223-4(F)

### ● Revision History

Date	Revision	Changes		
21.Aug.2012	001	New Release		
24.Sep.2012	002	New Release TO252-3 package.		
14.Mar.2013	003	Page 1.Series name is changed. Page 6. Append Thermal Resistance θja, θjc. Page 8. Figure 5, Page 9. Figure 11 All Quiescent current are integrated into Bias Current. Page 10. Figure 14, Page 11. Figure 15 All Quiescent current are integrated into Bias Current. Page 12. Figure 21, Page 13. Figure 24 All Quiescent current are integrated into Bias Current. Page 17, 18. Figure 25, 26, 27, 28 Power Dissipation is changed to be compliant with JEDEC standard. Page 19, 20. Calculation examples are changed. Page 25. "Application example" is deleted. Figure 29 " Example of the Parasitic Device Structures" is renewed.		
30.Sep.2013	004	AEC-Q100 Qualified Page 28. Physical Quantity is changed.		
01.May.2014	005	TO263-3F is changed to the individual registration.		
14.Jul.2014	006	Page 16. Output capacitor range was changed. Page 28. HTSOP-J8 Marking Diagrams is changed.		
17.Feb.2017	007	Improve the description, SOT223-4F to SOT223-4(F). Page 1. AEC-Q100 Grade postscript. Page 6. Thermal resistance is changed for JESD51-2A. Page 10. Revised Figure 13. Page 17, 18. Value of the power dissipation is changed. Page 23. Revised 7) in Operational Notes with change of Thermal resistance. Page 27. Add Physical Dimension, Tape and Reel Information of SOT223-4 package.		
19.Nov.2021	800	Add BD7xxU2EFJ-C Series.		

# **Notice**

#### **Precaution on using ROHM Products**

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(Note1) Medical Equipment Classification of the Specific Applications

( total) medical Equipment diagonisation of the opening, spinothering					
JAPAN	USA	EU	CHINA		
CLASSⅢ	CLASSⅢ	CLASS II b	CLASSIII		
CLASSIV	CLASSIII	CLASSⅢ	CLASSIII		

- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
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  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### **Precautions Regarding Application Examples and External Circuits**

- If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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